

C1 end  
3,3-dimethyl-4,4-diaminodicyclohexylmethane, 2-phenylethylamine, N,N-dimethyldipropylenetriamine, 3-[2-methoxyethoxy]propylamine, dimethylaminopropylamine, 1,4-bis(3-aminopropyl)piperazine, isophoronediamine, hexamethylenediamine, cyclohexyl-1,3-propanediamine, thiomicamine, (aminopropyl)-1,3-propanediamine, tetraethylenepentamine, tetramethylbutanediamine, propylamine, diaminopropanol, aminobutanol, (2-aminoethoxy)ethanol, and mixtures thereof, and (v) a polishing pad and/or an abrasive.

C2  
6. (Amended) The system of claim 3, wherein no abrasive is present in the system, and the polishing pad is a non-abrasive containing pad.

C3  
36. (Amended) A composition for polishing one or more layers of a multi-layer substrate that includes a first metal layer and a second layer comprising (i) liquid carrier, (ii) at least one oxidizing agent, (iii) at least one polishing additive that increases the rate at which the system polishes at least one layer of the substrate, and (iv) at least one stopping compound with a polishing selectivity of the first metal layer:second layer of at least about 30:1, wherein the stopping compound is a cationically charged nitrogen containing compound selected from the group consisting of a polyetheramine, polyethylenimine, N<sub>4</sub>-amino(N,N'-bis-[3-aminopropyl]ethylenediamine), 4,7,10-trioxatridecane-1,13-diamine, 3,3-dimethyl-4,4-diaminodicyclohexylmethane, 2-phenylethylamine, N,N-dimethyldipropylenetriamine, 3-[2-methoxyethoxy]propylamine, dimethylaminopropylamine, 1,4-bis(3-aminopropyl)piperazine, isophoronediamine, hexamethylenediamine, cyclohexyl-1,3-propanediamine, thiomicamine, (aminopropyl)-1,3-propanediamine, tetraethylenepentamine, tetramethylbutanediamine, propylamine, diaminopropanol, aminobutanol, (2-aminoethoxy)ethanol, and mixtures thereof, to be used with a polishing pad and/or an abrasive.

Please cancel claims 7-10 without prejudice or disclaimer of the subject matter contained therein.

Add the following claims:

C4  
52. (New) A system for polishing one or more layers of a multi-layer substrate that includes a first metal layer and a second layer comprising (i) a liquid carrier, (ii) at least one oxidizing agent, (iii) at least one polishing additive that increases the rate at which the system polishes at least one layer of the substrate, (iv) at least one stopping compound with a

polishing selectivity of the first metal layer:second layer of at least about 30:1, wherein the stopping compound is a cationically charged nitrogen containing compound selected from compounds comprising imines, amides, imides, and mixtures thereof, and (v) a polishing pad and/or an abrasive.

53. (New) The system of claim 52, wherein the liquid carrier is a nonaqueous solvent.

54. (New) The system of claim 52, wherein the liquid carrier is water.

55. (New) The system of claim 54, wherein the system comprises an abrasive suspended in the liquid carrier.

56. (New) The system of claim 54, wherein the abrasive is fixed on the polishing pad.

57. (New) The system of claim 54, wherein no abrasive is present in the system, and the polishing pad is a non-abrasive containing pad.

58. (New) The system of claim 54, wherein at least one stopping compound is selected from compounds comprising oligomeric imines, oligomeric amides, oligomeric imides, polymeric imines, polymeric amides, polymeric imides, and mixtures thereof.

59. (New) The system of claim 54, wherein at least one stopping compound is present in the liquid carrier in a concentration of about 5 wt.% or less.

60. (New) The system of claim 59, wherein at least one stopping compound is present in the liquid carrier in a concentration of about 3 wt.% or less.

61. (New) The system of claim 54, wherein at least one polishing additive is selected from the group consisting of a phosphorous-containing compound, a nitrogen-containing compound, a sulfur-containing compound, a carboxylic acid, and mixtures thereof.

62. (New) The system of claim 54, wherein the system further comprises at least one polymeric compound that reduces the polishing rate of at least one layer associated with the substrate.